FAIRCHILD

SEMICONDUCTOR

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74LVT322245 • 74LVTH322245

Low Voltage 32-Bit Transceiver with 3-STATE Outputs and 25 Ω Series Resistors in A Port Outputs

General Description

The LVT322245 and LVTH322245 contain thirty-two noninverting bidirectional buffers with 3-STATE outputs and are intended for bus oriented applications. The device is byte controlled. Each byte has separate control inputs which can be shorted together for full 32-bit operation. The T/\overline{R} inputs determine the direction of data flow through the device. The \overline{OE} inputs disable both the A and B ports by placing them in a high impedance state.

The LVT322245 and LVTH322245 are designed with equivalent 25Ω series resistance in both the HIGH and LOW states on the A Port outputs. This design reduces line noise in applications such as memory address drivers, clock drivers, and bus transceivers/transmitters.

The LVTH322245 data inputs include bushold, eliminating the need for external pull-up resistors to hold unused inputs.

These non-inverting transceivers are designed for low-voltage (3.3V) V_{CC} applications, but with the capability to provide a TTL interface to a 5V environment. The LVT322245 and LVTH322245 are fabricated with an advanced BiCMOS technology to achieve high speed operation similar to 5V ABT while maintaining a low power dissipation.

Features

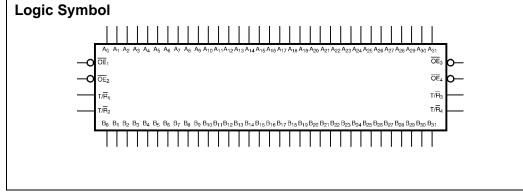
- \blacksquare Input and output interface capability to systems at 5V V_{CC}
- Bushold data inputs eliminate the need for external
- pull-up resistors to hold unused inputs (74LVTH322245)
- Also available without bushold feature (74LVT322245)
- Live insertion/extraction permitted
- Power Up/Power Down high impedance provides glitch-free bus loading
- A Port outputs include equivalent series resistance of 25Ω making external termination resistors unnecessary and reducing overshoot and undershoot
- A Port outputs source/sink ±12 mA
- B Port outputs source/sink –32 mA/+64 mA ■ ESD performance:
- Human-body model > 2000V
- Machine model > 200V
- Charged-device model > 1000V
- Packaged in plastic Fine-Pitch Ball Grid Array (FBGA)

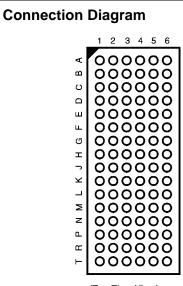
Ordering Code:

Order Number	Package Number	Package Description
74LVT322245G (Note 1) (Note 2)	BGA96A (Preliminary)	96-Ball Fine-Pitch Ball Grid Array (FBGA), JEDEC MO-205, 5.5mm Wide
74LVTH322245G (Note 1) (Note 2)	BGA96A	96-Ball Fine-Pitch Ball Grid Array (FBGA), JEDEC MO-205, 5.5mm Wide

Note 1: Ordering code "G" indicates TRAYS.

Note 2: Devices also available in TAPE and REEL. Specify by appending the suffix letter "X" to the ordering code.





(Top Thru View)

FBGA Pin Descriptions

Pin Names	Description
OE _n T/R _n	Output Enable Input (Active LOW)
	Transmit/Receive Input
A ₀ –A ₃₁ B ₀ –B ₃₁	Side A Inputs/3-STATE Outputs
B ₀ –B ₃₁	Side B Inputs/3-STATE Outputs

Pin Assignments for FBGA

	1	2	3	4	5	6
Α	B ₁	B ₀	T/R ₁	OE ₁	A ₀	A ₁
В	B ₃	B ₂	GND	GND	A ₂	A ₃
С	В ₅	B ₄	V _{CC1}	V _{CC1}	A ₄	A ₅
D	B ₇	B ₆	GND	GND	A ₆	A ₇
Е	B ₉	B ₈	GND	GND	A ₈	A ₉
F	В ₁₁	B ₁₀	V _{CC1}	V _{CC1}	A ₁₀	A ₁₁
G	B ₁₃	B ₁₂	GND	GND	A ₁₂	A ₁₃
н	B ₁₄	B ₁₅	T/R_2	OE ₂	A ₁₅	A ₁₄
J	B ₁₇	B ₁₆	T/R ₃	\overline{OE}_3	A ₁₆	A ₁₇
K	В ₁₉	B ₁₈	GND	GND	A ₁₈	A ₁₉
L	B ₂₁	B ₂₀	V _{CC2}	V _{CC2}	A ₂₀	A ₂₁
м	B ₂₃	B ₂₂	GND	GND	A ₂₂	A ₂₃
N	B ₂₅	B ₂₄	GND	GND	A ₂₄	A ₂₅
Р	B ₂₇	B ₂₆	V _{CC2}	V _{CC2}	A ₂₆	A ₂₇
R	B ₂₉	B ₂₈	GND	GND	A ₂₈	A ₂₉
Т	B ₃₀	B ₃₁	T/\overline{R}_4	\overline{OE}_4	A ₃₁	A ₃₀

Truth Tables

Inp	outs	Outpute
OE ₁	T/R ₁	Outputs
L	L	Bus B_0-B_7 Data to Bus A_0-A_7
L	Н	Bus $A_0 - A_7$ Data to Bus $B_0 - B_7$
Н	Х	HIGH-Z State on A ₀ -A ₇ , B ₀ -B ₇
Inp	outs	• • •
OE ₂	T/R ₂	Outputs

Bus B8-B15 Data to Bus A8-A15

		Outputs
OE ₃	T/R ₃	outputs
L	L	Bus B_{16} - B_{23} Data to Bus A_{16} - A_{23}
L	Н	Bus A ₁₆ -A ₂₃ Data to Bus B ₁₆ -B ₂₃
Н	Х	HIGH-Z State on A ₁₆ -A ₂₃ , B ₁₆ -B ₂₃
Inp	uts	Outpute
OE ₄	T/R ₄	Outputs
L	L	Bus B ₂₄ –B ₃₁ Data to Bus A ₂₄ –A ₃₁

Outputs

Bus A₂₄-A₃₁ Data to Bus B₂₄-B₃₁

HIGH-Z State on A24-A31, B24-B31

Inputs

Н

Х

L

Н

L	Н	Bus A ₈ -A ₁₅ Data to Bus B ₈ -B ₁₅
Н	Х	HIGH-Z State on A_8 - A_{15} , B_8 - B_{15}

L

H = HIGH Voltage Level L = LOW Voltage Level

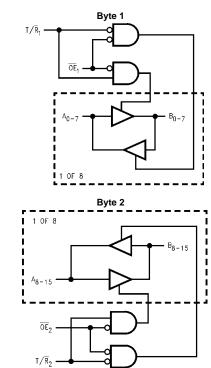
L

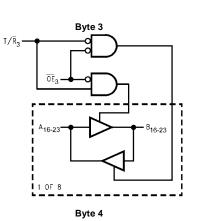
X = Immaterial Z = High Impedance

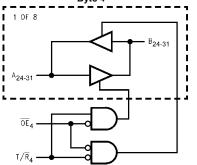
Functional Description

The LVT322245 and LVTH322245 contain thirty-two non-inverting bidirectional buffers with 3-STATE outputs. The device is byte controlled with each byte functioning identically, but independent of the other. The control pins can be shorted together to obtain 16-bit or full 32-bit operation.

Logic Diagrams







V_{CC1} is associated with Bytes 1 and 2.

 $\rm V_{\rm CC2}$ is associated with Bytes 3 and 4.

Note: Please note that these diagrams are provided only for the understanding of logic operations and should not be used to estimate propagation delays.

Symbol	Parameter	Value	Conditions	Units
V _{CC}	Supply Voltage	-0.5 to +4.6		V
VI	DC Input Voltage	-0.5 to +7.0		V
Vo	Output Voltage	-0.5 to +7.0	Output in 3-STATE	V
		-0.5 to +7.0	Output in HIGH or LOW State (Note 4)	- v
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA
I _{ОК}	DC Output Diode Current	-50	V _O < GND	mA
lo	DC Output Current	64	V _O > V _{CC} Output at HIGH State	
		128	V _O > V _{CC} Output at LOW State	mA
I _{CC}	DC Supply Current per Supply Pin	±64		mA
I _{GND}	DC Ground Current per Ground Pin	±128		mA
T _{STG}	Storage Temperature	-65 to +150		°C

Recommended Operating Conditions

Symbol	Parameter	Min	Max	Units		
V _{CC}	Supply Voltage		2.7	3.6	V	
VI	Input Voltage		0	5.5	V	
I _{OH}	HIGH Level Output Current	B Port		-32	mA	
		A Port		-12	ШA	
I _{OL}	LOW Level Output Current	B Port		64	س ۸	
		A Port		12	mA	
T _A	Free Air Operating Temperature		-40	+85	°C	
$\Delta t / \Delta V$	Input Edge Rate, V _{IN} = 0.8V–2.0V, V _{CC} = 3.0V		0	10	ns/V	

Note 3: Absolute Maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum rated conditions is not implied.

Note 4: I_O Absolute Maximum Rating must be observed.

DC Electrical Characteristics

Symbol	Param	otor	V _{cc}	$T_A = -40^{\circ}C$	c to +85°C	Units	Conditions
Symbol	Paran	leter	(V)	Min	Max	Units	Conditions
V _{IK}	Input Clamp Diode Voltage		2.7		-1.2	V	I _I = -18 mA
VIH	Input HIGH Voltage		2.7-3.6	2.0		V	$V_{O} \le 0.1 V$ or
V _{IL}	Input LOW Voltage		2.7-3.6		0.8	V	$V_{O} \ge V_{CC} - 0.1V$
V _{OH}	Output HIGH Voltage	A Port	3.0	2.0		V	I _{OH} = -12 mA
	B Port	A Pon	2.7-3.6	V _{CC} - 0.2		V	I _{OH} = -100 μA
		D Dort	2.7	2.4		V	I _{OH} = -8 mA
		BPOIL	3.0	2.0		v	I _{OH} = -32 mA
V _{OL}	Output LOW Voltage	A Port	3.0		0.8	V	I _{OL} = 12 mA
	B Port	APOIL	2.7		0.2	V	I _{OL} = 100 μA
			2.7		0.5		I _{OL} = 24 mA
		R Port	3.0		0.4	V	I _{OL} = 16 mA
		BFOIL	3.0		0.5	v	I _{OL} = 32 mA
			3.0		0.55		I _{OL} = 64 mA
I _{I(HOLD)}	Bushold Input Minimum Drive		3.0	75		μA	$V_{I} = 0.8V$
(Note 5)			5.0	-75		μΑ	V _I = 2.0V
I _{I(OD)}	Bushold Input Over-Drive	shold Input Over-Drive 3.0 500		μA	(Note 6)		
(Note 5)	Current to Change State			-500		μΛ	(Note 7)
l _l	Input Current		3.6		10		V _I = 5.5V
		Control Pins	3.6		±1	μA	$V_I = 0V \text{ or } V_{CC}$
		Data Pins	3.6		-5	μΑ	$V_I = 0V$
	Data Pins		3.0		1		$V_I = V_{CC}$
IOFF	Power Off Leakage Current	•	0		±100	μA	$0V \le V_1 \text{ or } V_0 \le 5.5V$

DC Electrical Characteristics (Cont

Symbol	Parameter		V _{cc}	$T_A = -40^{\circ}C$ to $+85^{\circ}C$		Units	Conditions
Gymbol	i alameter	(V)	Min Max		Onita	Conditions	
I _{PU/PD}	Power Up/Down		0–1.5V		±100	μA	V _O = 0.5V to 3.0V
	3-STATE Current		0 1.01			μοι	$V_I = GND$ to V_{CC}
I _{OZL}	3-STATE Output Leakage Current		3.6		-5	μA	V _O = 0.5V
I _{OZL} (Note 5)	3-STATE Output Leakage Current		3.6		-5	μA	V _O = 0.0V
I _{OZH}	3-STATE Output Leakage Current		3.6		5	μA	V _O = 3.0V
I _{OZH} (Note 5)	3-STATE Output Leakage Current		3.6		5	μA	V _O = 3.6V
I _{OZH} +	3-STATE Output Leakage Current		3.6		10	μA	$V_{CC} < V_O \le 5.5V$
I _{CCH}	Power Supply Current	V _{CC1} or V _{CC2}	3.6		0.19	mA	Outputs HIGH
I _{CCL}	Power Supply Current	V _{CC1} or V _{CC2}	3.6		5	mA	Outputs LOW
I _{CCZ}	Power Supply Current	V_{CC1} or V_{CC2}	3.6		0.19	mA	Outputs Disabled
I _{CCZ} +	Power Supply Current	V_{CC1} or V_{CC2}	3.6		0.19	mA	$V_{CC} \le V_O \le 5.5V$,
			210				Outputs Disabled
Δl _{CC}	Increase in Power Supply Current		3.6		0.2	mA	One Input at V _{CC} – 0.6V
	(Note 8)	V _{CC1} or V _{CC2}	0.0		0.2	IIIA	Other Inputs at V _{CC} or GND

Note 5: Applies to bushold versions only (74LVTH322245).

Note 6: An external driver must source at least the specified current to switch from LOW-to-HIGH.

Note 7: An external driver must sink at least the specified current to switch from HIGH-to-LOW.

Note 8: This is the increase in supply current for each input that is at the specified voltage level rather than V_{CC} or GND.

Dynamic Switching Characteristics (Note 9)

Symbol	Parameter	V _{cc}	T _A = 25°C			Units	Conditions	
Cymbol	i al allieter	(V)	Min	Тур	Max	onits	$\textbf{C}_{\textbf{L}} = \textbf{50} \; \textbf{pF} \; \textbf{R}_{\textbf{L}} = \textbf{500} \boldsymbol{\Omega}$	
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	3.3		0.8		V	(Note 10)	
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	3.3		-0.8		V	(Note 10)	

Note 9: Characterized in SSOP package. Guaranteed parameter, but not tested.

Note 10: Max number of outputs defined as (n). n–1 data inputs are driven 0V to 3V. Output under test held LOW.

AC Electrical Characteristics

Symbol	Parameter	$T_A = -40^{\circ}$ C to +85°C C _L = 50 pF, R _L = 500 Ω				Units
		Min	Max	Min	Max	1
		t _{PLH}	Propagation Delay Data to A Port Output	1.0	4.0	1.0
t _{PHL}		1.0	3.7	1.0	4.1	ns
t _{PLH}	Propagation Delay Data to B Port Output	1.0	3.5	1.0	3.9	
t _{PHL}		1.0	3.5	1.0	3.9	ns
t _{PZH}	Output Enable Time for A Port Output	1.0	5.3	1.0	6.3	
t _{PZL}		1.0	5.6	1.0	7.2	ns
t _{PZH}	Output Enable Time for B Port Output	1.0	4.6	1.0	5.4	ns
t _{PZL}		1.0	5.3	1.0	6.9	115
t _{PHZ}	Output Disable Time for A Port Output	1.5	5.6	1.5	6.3	ns
t _{PLZ}		1.5	5.5	1.5	5.5	115
t _{PHZ}	Output Disable Time for B Port Output	1.5	5.4	1.5	6.1	
t _{PLZ}		1.5	5.1	1.5	5.4	ns

Capacitance (Note 11)

Symbol	Parameter	Conditions	Typical	Units
CIN	Input Capacitance	$V_{CC} = 0V, V_I = 0V \text{ or } V_{CC}$	4	pF
C _{I/O}	Input/Output Capacitance	$V_{CC} = 3.0V$, $V_{O} = 0V$ or V_{CC}	8	pF
Note 11: Capacitance	is measured at frequency f = 1 MHz, per	MIL-STD-883, Method 3012.		

